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PCN #230
Notification Date:
March 18, 2022

Product / Process Change Notice

Parts Affected:

Chip process CPD102X, Schottky diodes, wafers, and bare die.

Extent of Change:

The CPD102X wafer process has been discontinued and is being replaced with the CPD51V wafer process. See Figures 1 and 2 for details.

Reason for Change:

The CPD102X wafer process has been replaced in order to enhance manufacturing process controls. This change will help ensure an undisrupted supply of product.

Effect of Change:

The CPD51V wafer process meets all electrical specifications of the individual devices listed on the following page.

Qualification:

P/N: CPD51V Chip Process

Package: SOT-23 Case

No.	Test	Conditions (Reference standards are in bold)	Qty	Pass/Fail	Test Results
1	Device Life Tests				
A	High Temperature Storage Life (HTSL - "Bake test")	150°C (-0/+10)°C or specified temperature. 1000 hours. JESD22-A103	77	Pass	77/77
B	High Temperature Reverse Bias (HTRB)	T=150°C, t = 1000 hours Bias conditions per device datasheet. JESD22-A108	77	Pass	77/77
C	Steady State Operational Live (SSOP)	Ta=25°C, Tj>=125°C Io = 330mA MIL-STD-750 TM1037 & JESD22-A105	77	Pass	77/77
D	Temperature Cycling (TC)	1000 cycles. Dwell time = 15 min Ta = -55°C to +150°C JESD22-A104 & MIL-STD-750 TM1051.	77	Pass	77/77

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Earliest Effective Date of Change:

March 18, 2022

Sample Availability:

Please contact your salesperson or manufacturer's representative for samples.

Figure 1: CPD102X Chip Geometry (Discontinued)

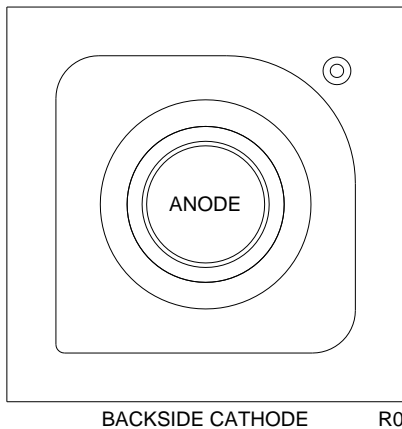
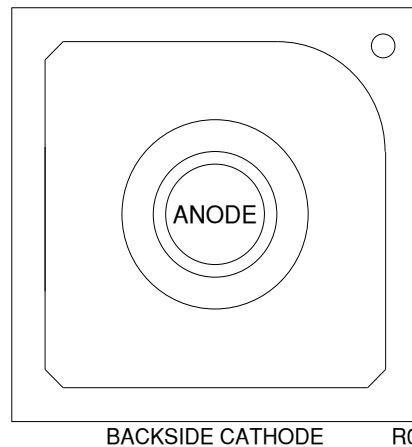


Figure 2: CPD51V Chip Geometry



Wafer Diameter: 5 inch
Die Size: 9.06 x 9.06 mils
Die Thickness: 5.9 mils
Bond Pad Size (Anode): 4.8 mils diameter
Topside Metal: Al (30,000Å)
Backside Metal: Au (9,000Å)

Wafer Diameter: 6 inch
Die Size: 11.8 x 11.8 mils
Die Thickness: 7.1 mils
Bond Pad Size (Source): 5.12 mils diameter
Topside Metal: Al (30,000Å)
Backside Metal: Au (12,000Å)

Part Numbers Affected:

CEN1267	CMPD6263S	CPD102X-CMPD6263-CT
CMDD6263	CMSD6263	CPD102X-CMPD6263-WN
CMKD6263DO	CMSD6263A	CPD102X-CMPD6263-WR
CMLD6263C	CMSD6263C	CPD102X-1N5711-WN
CMLD6263DO	CMSD6263S	CPD102X-1N6263-WN
CMOD6263	CMUD6263AE	
CMPD6263	CMUD6263CE	
CMPD6263A	CMUD6263E	
CMPD6263C	CMUD6263SE	



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As per JEDEC standard JESD46, Customer Notification of Product/Process Changes by Solid-State Suppliers, a lack of acknowledgement of a PCN within thirty (30) days constitutes acceptance of the change.

The undersigned acknowledges and accepts Central Semiconductor's Product/Process Change Notification (PCN).

Company Name:	
Address:	
Printed Name:	
Title:	
Signature:	
Date:	